

Date: 2004-09-05

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D121

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- S5: (505929) growth
- S6: (80308) epitaxial
- S7: (508323) selective
- S8: (3751) nonselective
- S9: (10682) non adj selective
- S10: (13714) nonselective (non adj selective)
- S11: (32926) epitaxial adj growth
- S12: (47) (nonselective (non adj selective)) adj (epitaxial adj growth)
- S13: (29) ((nonselective (non adj selective)) adj (epitaxial adj growth))
- S14: (110307) single adj crystal\$3 monocrystal\$3 mono adj crystal\$3
- S15: (188733) (polysilicon poly adj silicon polycrystal\$4 poly adj crystal\$4)
- S16: (320407) collector
- S17: (17007) (single adj crystal\$3 monocrystal\$3 mono adj crystal\$3)
- S18: (227) ((single adj crystal\$3 monocrystal\$3 mono adj crystal\$3)) v
- S19: (189) (((single adj crystal\$3 monocrystal\$3 mono adj crystal\$3)) v
- S20: (17) (((single adj crystal\$3 monocrystal\$3 mono adj crystal\$3)) v
- S21: (2111568) thick\$4
- S22: (18) (((single adj crystal\$3 monocrystal\$3 mono adj crystal\$3)) v
- S23: (3) "05062991"
- S24: (2) "5323032".pn.

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((single adj crystal\$3 monocrystal\$3 mono adj crystal\$3)
) with ((polysilicon poly adj silicon polycrystal\$4 poly adj crystal\$4)
)) with collector) with thick\$4

Jen. 2005

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	U	I	Inventor	Document Issue P	Title	Current	Current X	Retrieval	S	C	P	Image	Do:P
1	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Sato, Hideki	US 2004012004	2 Semiconductor device and method for	257/19			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200407
2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Chen, Huai	US 2004012004	8 Self-aligned mask formed utilizing diffe	438/16			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200407
3	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Washio, Ka	US 2003022003	4 Semiconductor device	257/19	257/E21.3		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200307
4	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	YAMAZAKI, Y	US 2001002001	2 A METHOD OF PRODUCING A SEMIC	438/49	257/E21.3		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200107
5	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Heinemann	US 6740582004	1 Bipolar transistor and method for prod	438/30	257/197		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 674057
6	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Sato, Fumi	US 6680522004	3 Semiconductor device with reduced el	257/58	257/587		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 668057
7	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Washio, Ka	US 6800172003	3 Heterojunction bipolar transistor	257/19	257/191		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 680017
8	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Ehwald, Ka	US 6465312002	6 Bipolar transistor and method for prod	438/34	257/E21.1		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 646531
9	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Marty, Michael	US 6465312002	7 Process for producing a bipolar transi	438/32	257/E21.3		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 646531
10	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Laurens, M	US 8171892001	1 Method of manufacturing BICMOS inte	438/20	257/E21.6		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 617189

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